

of forming the molding portion is carried out while a convexity portion of a press die being butted to at least the electrode layer on the substrate film.

15. (Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the step of forming the molding portion in the substrate film is carried out by cold processing at a temperature lower than the thermal deformation.

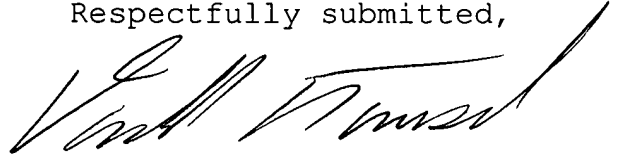
16. (Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the step of disposing the conductive layer to the molding portion includes a step of promoting gelling of conductive gel composing the conductive layer.

REMARKS

The amendments to Claims 1, 3-5 and 13-16, are made to eliminate the multiple dependencies, to place the claims in proper U.S. format, and to conform claim 1 to claim 1 as amended in the amendment filed in the international application on April 10, 2001. The present amendment is deemed not to add new matter. Claims 1-17 are in the application.

It is respectfully submitted that this application is now in condition for examination on the merits and early action and allowance thereof is accordingly respectfully requested.

Respectfully submitted,



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MARKED-UP VERSION OF AMENDED CLAIMS 1, 3-5 AND 13-16:

1. (Amended) An electrode structure for an iontophoresis device comprising:

a backing having a substrate film having a molding portion,
an electrode layer formed passing the outer circumferential
portion from the inner bottom of the molding portion, [and]

an insulating layer formed in at least the outer circumferential
portion of the molding portion and also in the upper portion of the
electrode layer[;],

a conductive layer formed in the molding portion[;], and

a cover member for [protecting] covering the conductive layer
and the insulating layer in a separable manner.

3. (Amended) The electrode structure for the iontophoresis
device according to claim 1 [or claim 2], wherein the sinking depth
in the molding portion of the substrate film is in a range of 0.5
mm to 7.5 mm.

4. (Amended) The electrode structure for the iontophoresis
device according to [any one of claims] claim 1 [to 3], wherein the
molding angle in the molding portion of the substrate film is in
a range of 5° to 70°.

5. (Amended) The electrode structure for the iontophoresis
device according to [any one of claims] claim 1 [to 4], wherein the
cover member is to seal the conductive layer between the insulating

layer and itself in a separable manner, thereby allowing the conductive layer to be kept in a sealed state.

13. (Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11 [or claim 12], wherein the method further comprises a step of supplying an adhesive sheet to the rear face of the substrate film and cutting the sheet into a predetermined shape.

14. (Amended) The method of producing the electrode structure for the iontophoresis device according to [any one of claims] claim 11 [to 13], wherein the step of forming the molding portion is carried out while a convexity portion of a press die being butted to at least the electrode layer on the substrate film.

15. (Amended) The method of producing the electrode structure for the iontophoresis device according to [any one of claims] claim 11 [to 14], wherein the step of forming the molding portion in the substrate film is carried out by cold processing at a temperature lower than the thermal deformation.

16. (Amended) The method of producing the electrode structure for the iontophoresis device according to [any one of claims] claim 11 [to 15], wherein the step of disposing the conductive layer to the molding portion includes a step of promoting gelling of conductive gel composing the conductive layer.

CLAIMS

1. An electrode structure for an iontophoresis device comprising: a backing having a substrate film having a molding portion, an electrode layer formed passing the outer circumferential portion from the inner bottom of the molding portion, and an insulating layer formed in at least the outer circumferential portion of the molding portion and also in the upper portion of the electrode layer; a conductive layer formed in the molding portion; and a cover member for protecting the conductive layer.
2. The electrode structure for the iontophoresis device according to claim 1, wherein an adhesive sheet is installed in the rear face of the substrate film of the backing.
3. The electrode structure for the iontophoresis device according to claim 1 or claim 2, wherein the sinking depth in the molding portion of the substrate film is in a range of 0.5 mm to 7.5 mm.
4. The electrode structure for the iontophoresis device according to any one of claims 1 to 3, wherein the molding angle in the molding portion of the substrate film is in a range of 5° to 70°.
5. The electrode structure for the iontophoresis device according to any one of claims 1 to 4, wherein the cover member is to seal the conductive layer between the insulating layer and itself in a separable manner, thereby allowing the conductive layer to be kept in a sealed state.
6. The electrode structure for the iontophoresis device according to claim 5, wherein the separation mechanism between